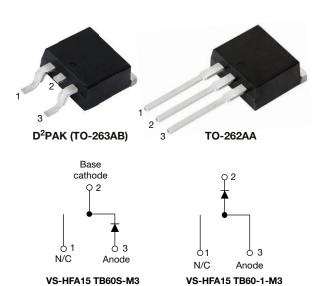


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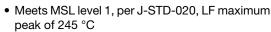
# HEXFRED®, Ultrafast Soft Recovery Diode, 15 A



PRIMARY CHARACTERISTICS						
I <sub>F(AV)</sub>	15 A					
$V_{R}$	600 V					
V <sub>F</sub> at I <sub>F</sub>	1.2 V					
t <sub>rr</sub> (typ.)	23 ns					
T <sub>J</sub> max.	150 °C					
Package	D <sup>2</sup> PAK (TO-263AB), TO-262AA					
Circuit configuration	Single					

### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>





- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **BENEFITS**

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

#### **DESCRIPTION**

VS-HFA15TB60S, VS-HFA15TB60-1 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the VS-HFA15TB60S. VS-HFA15TB60-1 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and sizes. The HEXFRED VS-HFA15TB60S, VS-HFA15TB60-1 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	$V_{R}$		600	V			
Maximum continuous forward current	l <sub>F</sub>	T <sub>C</sub> = 100 °C	15				
Single pulse forward current	I <sub>FSM</sub>		150	Α			
Maximum repetitive forward current	I <sub>FRM</sub>		60				
Maximum power discination	Б	T <sub>C</sub> = 25 °C	74	W			
Maximum power dissipation	$P_{D}$	T <sub>C</sub> = 100 °C	29	VV			
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C			



Series inductance

 $L_{S}$ 

## VS-HFA15TB60S-M3, VS-HFA15TB60-1-M3

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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA		600	-	-		
		I <sub>F</sub> = 15 A		-	1.3	1.7	V	
Maximum forward voltage	$V_{FM}$	I <sub>F</sub> = 30 A	See fig. 1	-	- 1.5	2.0	]	
		I <sub>F</sub> = 15 A, T <sub>J</sub> = 125 °C		-	1.2	1.6		
Maximum reverse		V <sub>R</sub> = V <sub>R</sub> rated	Coo fig. 0	-	1.0	10		
leakage current	I <sub>RM</sub>	$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 ^{\circ}\text{X} V_R \text{ rated}$	See fig. 2	-	400	1000	μΑ	
Junction capacitance	Ст	$V_{\rm p} = 200 \text{ V}$	See fig. 3	_	25	50	рF	

Measured lead to lead 5 mm from package body

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST COM	TEST CONDITIONS				UNITS	
Reverse recovery time See fig. 5	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	√μs, V <sub>R</sub> = 30 V	-	23	-		
	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	50	60	ns	
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	105	120		
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.5	6.0	А	
See fig. 6	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C	$I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	6.5	10		
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	84	180	nC	
See fig. 7	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	241	600		
Peak rate of fall of recovery current during t <sub>b</sub> See fig. 8	dI <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	188	-		
	dI <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	160	-	A/µs	

THERMAL - MECHAI	THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	MIN. TYP.		UNITS		
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	1.7			
Thermal resistance, junction-to-ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	K/W		
Thermal resistance, case-to-heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth, and greased	-	0.5	-			
Weight			-	2.0	-	g		
vveigni			-	0.07	-	OZ.		
Madding daying		Case style D <sup>2</sup> PAK (TO-263AB)	HFA15TB60S					
Marking device		Case style TO-262AA		HFA15	TB60-1			



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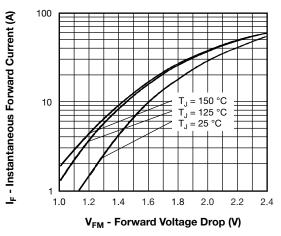


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

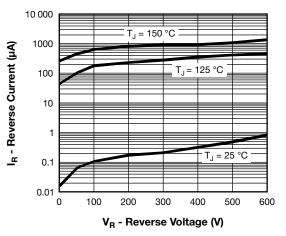


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

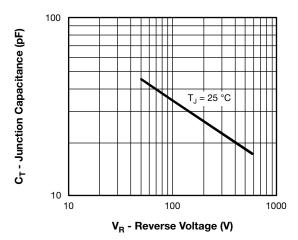


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

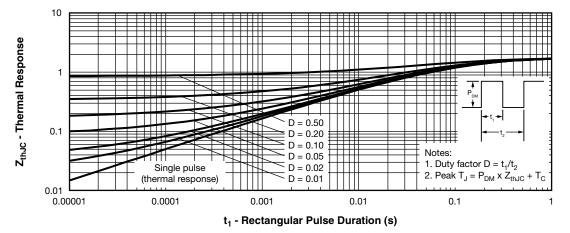


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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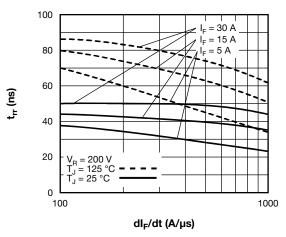


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

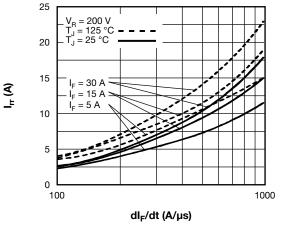


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

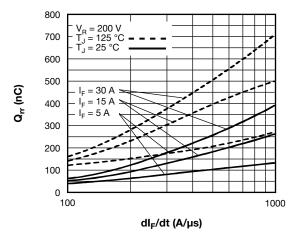


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

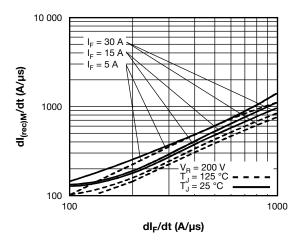
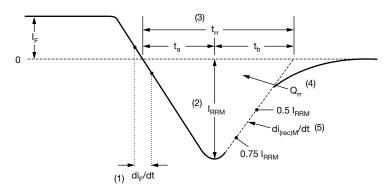


Fig. 8 - Typical  $dI_{(rec)M}/dt$  vs.  $dI_F/dt$ 



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_{r}$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $\mathbf{Q}_{rr}$  area under curve defined by  $\mathbf{t}_{rr}$  and  $\mathbf{I}_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

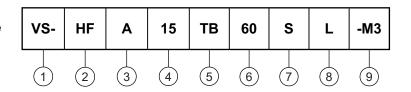
Fig. 9 - Reverse Recovery Waveform and Definitions

### VS-HFA15TB60S-M3, VS-HFA15TB60-1-M3

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#### **ORDERING INFORMATION TABLE**

#### Device code



1 - Vishay Semiconductors product

- HEXFRED® family

3 - Electron irradiated

4 - Current rating (15 = 15 A)

Fackage: TB = TO-220

6 - Voltage rating (60 = 600 V)

 $\overline{7}$  - • S = D<sup>2</sup>PAK (TO-263AB)

• -1 = TO-262AA

8 - • None = tube (50 pieces)

• L = tape and reel (left oriented, for D2PAK (TO-263AB) package )

• R = tape and reel (right oriented, for D<sup>2</sup>PAK (TO-263AB) package)

9 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER TUBE OR TAPE AND REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-HFA15TB60S-M3	50	1000	Antistatic plastic tube				
VS-HFA15TB60SL-M3	800	800	13" diameter reel				
VS-HFA15TB60SR-M3	800	800	13" diameter reel				
VS-HFA15TB60-1-M3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS							
Dimensions	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96164					
Dimensions	TO-262AA	www.vishay.com/doc?96165					
Dark manding information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?95444					
Part marking information	TO-262AA	www.vishay.com/doc?95443					
Packaging information		www.vishay.com/doc?96424					
SPICE model		www.vishay.com/doc?95357					



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### D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	STINIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070		Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

#### Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164

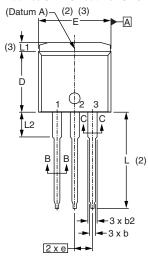


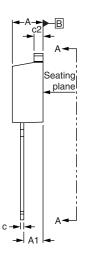
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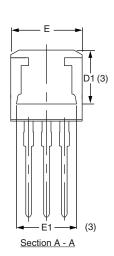
### **TO-262AA**

### **DIMENSIONS** in millimeters and inches

#### Modified JEDEC® outline TO-262







**⊕** 0.010 **M** A**M** B

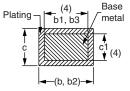
#### Lead assignments



**Diodes** 1. - Anode (two die)/open (one die)

2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

SYMBOL	MILLIM	IETERS	INC	INCHES			
	MIN.	MAX.	MIN.	MAX.	NOTES		
A 4.06		4.83	0.160	0.190			
A1	2.03	3.02	0.080	0.119			
b	0.51	0.99	0.020	0.039			
b1	0.51	0.89	0.020	0.035	4		
b2	1.14	1.78	0.045	0.070			
b3	1.14	1.73	0.045	0.068	4		
С	0.38	0.74	0.015	0.029			
c1	0.38	0.58	0.015	0.023	4		
c2	1.14 1.6		0.045	0.065			
D	8.51	9.65	0.335	0.380	2		
D1	6.86	8.00	0.270	0.315	3		
Е	9.65	10.67	0.380	0.420	2, 3		
E1	7.90	8.80	0.311	0.346	3		
е	2.54	BSC	0.10	0 BSC			
L	13.46	14.10	0.530	0.555			
L1	-	1.65	-	0.065	3		
L2	3.56	3.71	0.140	0.146			

#### **Notes**

(4) Dimension b1 and c1 apply to base metal only

Controlling dimension: inches

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)



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